

TO-92 Plastic-Encapsulate Transistors

KTC3194 TRANSISTOR (NPN)

FEATURES

- General Purpose Switching Application

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

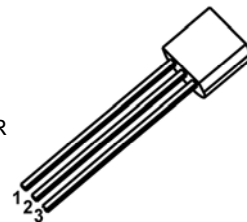
Symbo	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	0.02	A
P_C	Collector Power Dissipation	0.625	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

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1.EMITTER

2.COLLECTOR

3.BASE



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15\text{mA}, I_B=1.5\text{mA}$			0.2	V
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=1\text{mA}$		550		MHz

CLASSIFICATION OF h_{FE}

RANK	R	O	Y
RANGE	40-80	70-140	100-200